

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



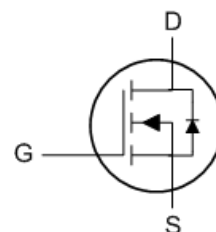
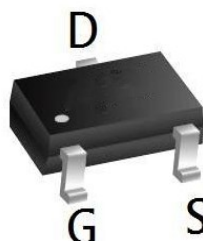
BVDSS	RDS(on)	ID
30V	12mΩ	7.0A

Description

The XR3410L is the high cell density trenched N-ch MOSFETs, which provides excellent RDS(on) and efficiency for most of the small power switching and load switch applications.

The XR3410L meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.0	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.5	A
I_{DM}	Pulsed Drain Current ²	29.4	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	85	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	12	17	mΩ
		V _{GS} =4.5V, I _D =5A	-	17	25	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	614	-	pF
C _{oss}	Output Capacitance		-	118	-	pF
C _{rss}	Reverse Transfer Capacitance		-	98	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =11A, V _{GS} =10V	-	16	-	nC
Q _{gs}	Gate-Source Charge		-	2.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V,R _L =1.35Ω, R _{GEN} =3Ω, V _{GS} =10V	-	6	-	ns
t _r	Turn-on Rise Time		-	10	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	6.5	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =15A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =11A,dl/dt=500A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	10	-	nC

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	7	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=8A, di/dt=100A/\mu s,$ $T_J=25^\circ C$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.9	---	nC

Note :

N-Ch 30V Fast Switching MOSFETs

Figure1: Output Characteristics

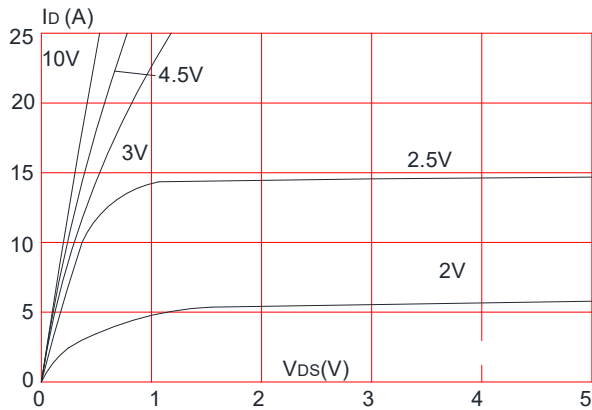


Figure 2: Typical Transfer Characteristics

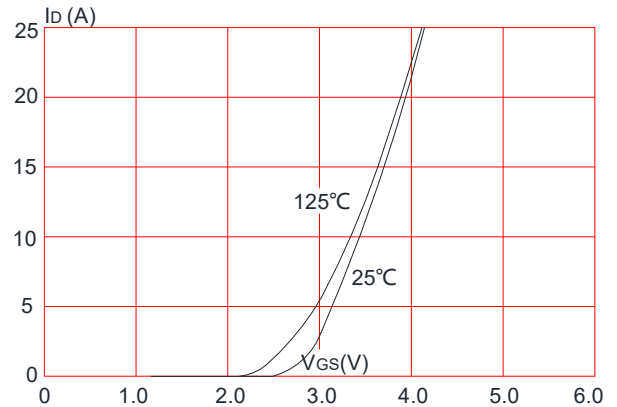


Figure 3: On-resistance vs. Drain Current

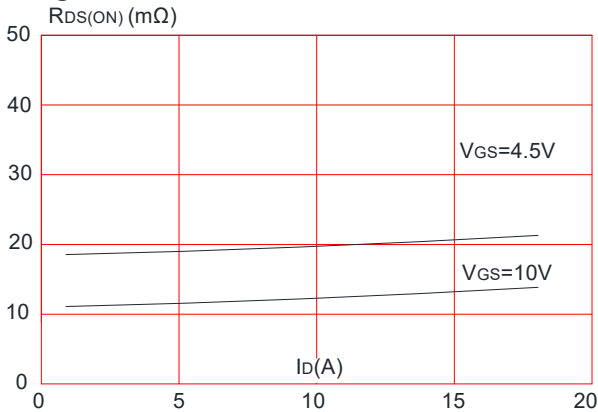


Figure 4: Body Diode Characteristics

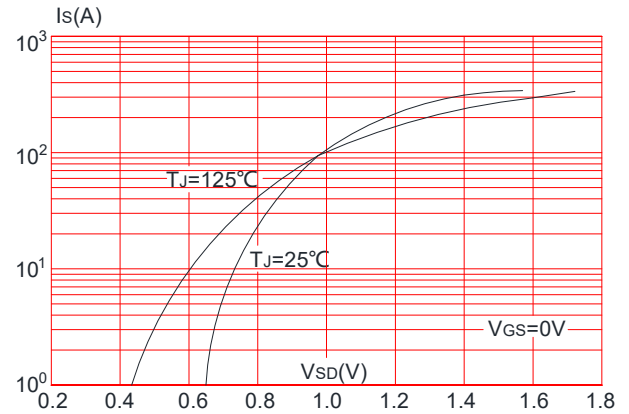


Figure 5: Gate Charge Characteristics

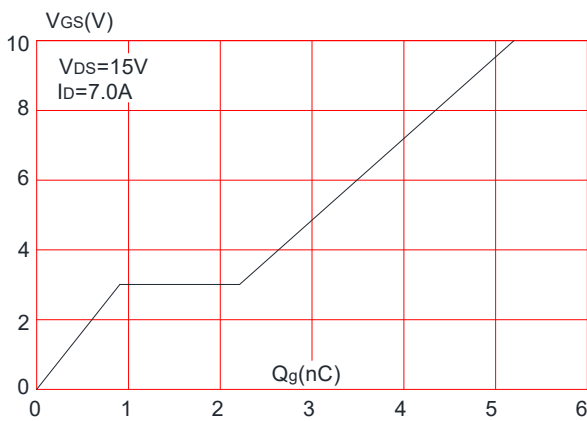


Figure 6: Capacitance Characteristics

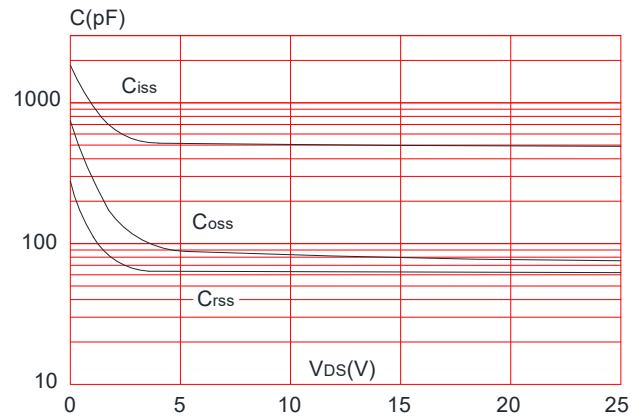


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

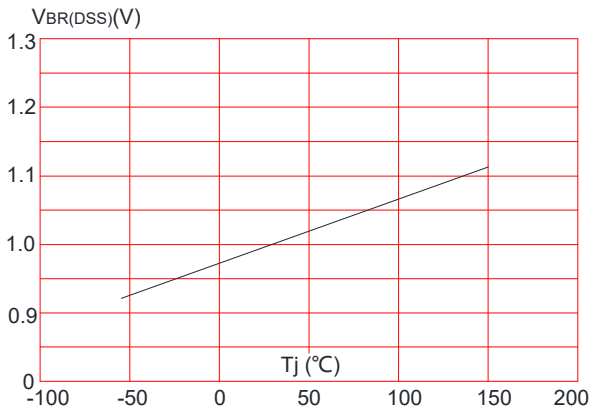


Figure 8: Normalized on Resistance vs. Junction Temperature

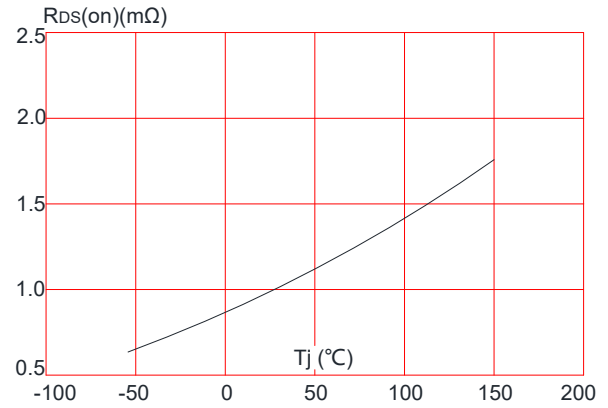


Figure 9: Maximum Safe Operating Area

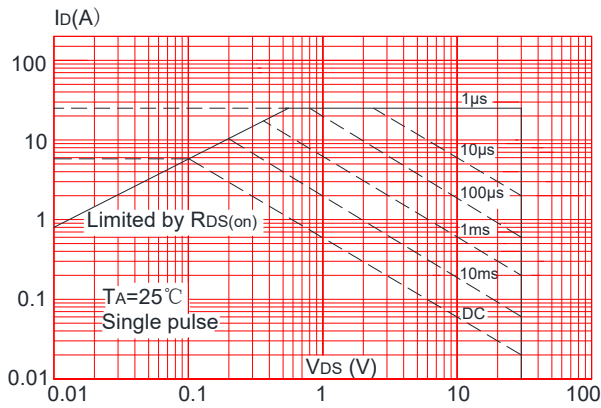


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

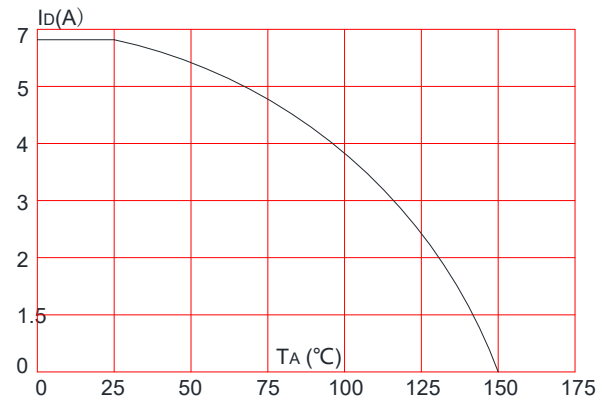
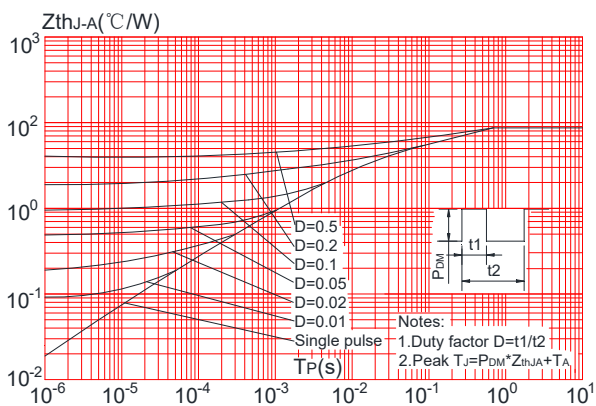
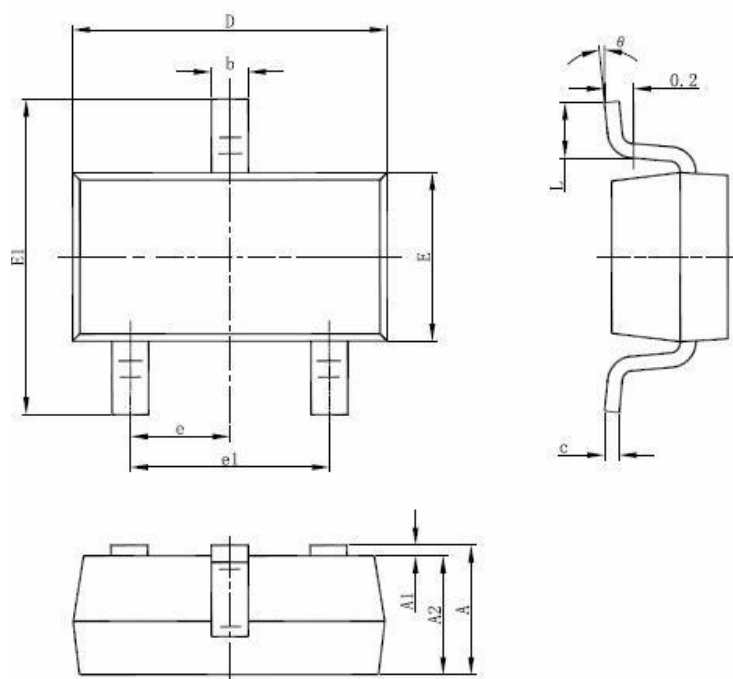


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°